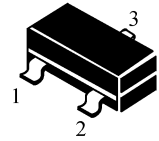


Excellent H_{FE} Linearity H_{FE} $H_{FE}(0.1mA)/h_{FE}(2mA)=0.95(Typ.)$
 High H_{FE} H_{FE} $H_{FE}=200\ 700$
 Low Noise $NF=1dB(Typ.),10dB(Max.)$.
 Complementary to S9015(GM9015) S9015(GM9015)

SOT-23

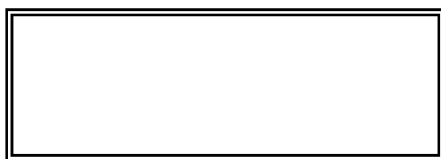
- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

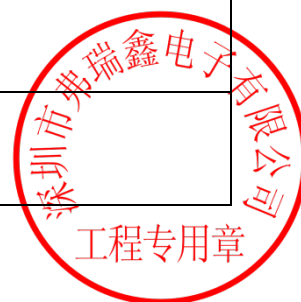


CHARACTERISTIC	Symbol	Rating	Unit
Collector-Base Voltage -	V_{CBO}	50	Vdc
Collector-Emitter Voltage -	V_{CEO}	45	Vdc
Emitter-Base Voltage -	V_{EBO}	5.0	Vdc
Collector Current-Continuous -	I_C	150	mAdc
Base Current	I_B	30	mAdc
Collector Power Dissipation	P_C	225	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	



Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=50V, I_E=0$	—	—	0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5V, I_C=0$	—	—	0.1	μA
Collector-Base Breakdown Voltage -	$V_{(BR)CBO}$	$I_C=100\mu A$	50	—	—	V
Collector-Emitter Breakdown Voltage -	$V_{(BR)CEO}$	$I_C=1.0mA$	45	—	—	V
Emitter-Base Breakdown Voltage -	$V_{(BR)EBO}$	$I_E=100\mu A$	5	—	—	V
DC Current Gain	h_{FE}	$V_{CE}=6V, I_C=2mA$	200	—	700	—
Collector-Emitter Saturation Voltage -	$V_{CE(sat)}$	$I_C=100mA, I_B=5mA$	—	—	0.3	V
Base-Emitter Voltage -	V_{BE}	$V_{CE}=5.0V, I_C=10mA$	—	—	0.82	V
Transition Frequency	f_T	$V_{CE}=5.0V, I_C=10mA$	100	180	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0,$ $f=1MHz$	—	4.0	7.0	pF





外形封装尺寸

